

# SiC - photodiode JEC 0,1 IS



- characteristics :**
- ◆ spectral range 210 ... 380 nm
  - ◆ active area 0,055 mm<sup>2</sup>
  - ◆ high UV-responsivity 0,13 A/W
  - ◆ TO 18-package
  - ◆ photodiode isolated to package

- applications :**
- ◆ UV-measurements only
  - ◆ UV-source control
  - ◆ flame detection

**maximum ratings:**

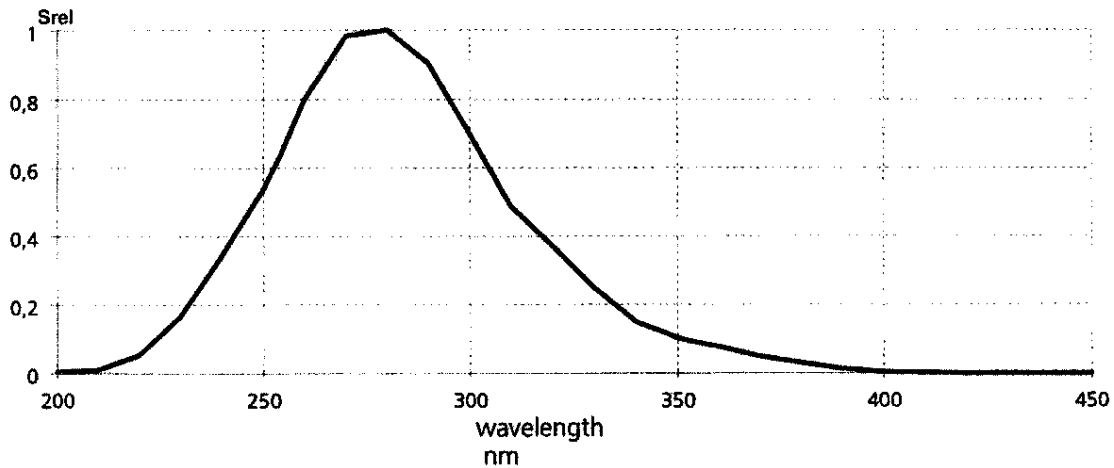
reverse voltage	20	V
operation temperature range	- 25 °C ... 70	°C
storage temperature range	0 °C ... 100	°C
soldering temperature (3s)	260	°C

**technical data :**

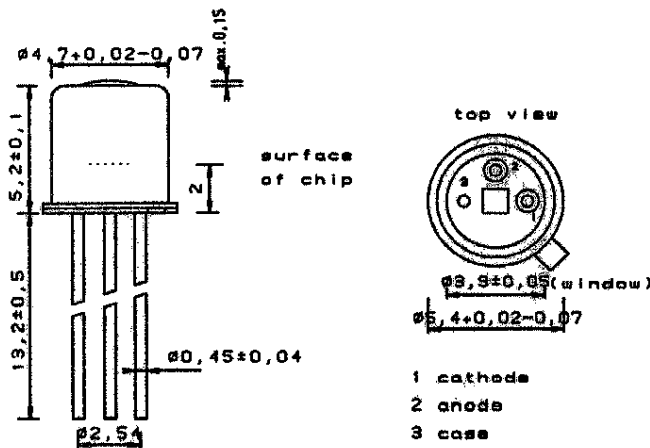
test conditions, as not otherwise specified:  $\gamma_a = 25 \text{ °C}$ ,  $V_R = 0V$

parameters	test conditions	min.	typ.	max.	unit
active area			0,25 x 0,25		mm <sup>2</sup>
spectral range		210		380	nm
maximum of spectral responsivity	$\lambda_{max} = 275 \text{ nm}$		0,13		A/W
absolute spectral responsivity	$\lambda = 254 \text{ nm}$		0,11		A/W
dark current $I_R$	$V_R = 1 \text{ V}$		1		fA
short current (sun light)	bright sun cloudy		50 20		nA
capacitance			21		pF

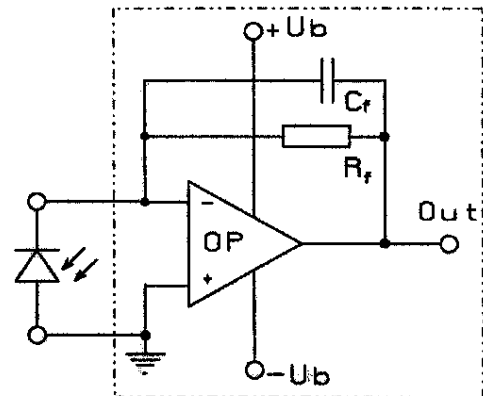
## relative spectral responsivity



## package dimensions



## application example



The application example shows a typical circuit.  $R_f$  is responsible for the gain of the circuit.  $C_f$  compensates the reverse junction capacitance of the photodiode and input capacitance of the OPV. The exact value of  $C_f$  depends on  $R_f$ , used OPV and capacitance of the circuit. A typical value is 1 pF.

The diagram shows dependence of amplitude of the application circuit with OPA 111,  $R_f = 50 \text{ M}\Omega$  and  $C_f = 0.5 \text{ pF}$ .

